

GSDBAS16

Switching Diode

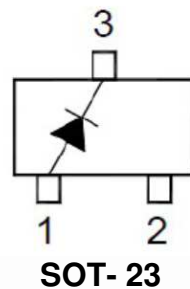
Product Description

Switching Diode 215mA / 75V

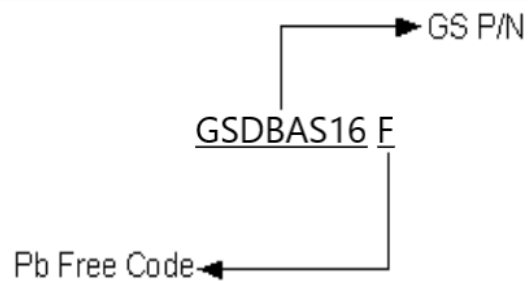
Features

- Low forward voltage
- Fast reverse recovery time
- Halogen-Free part

Packages



Ordering Information



Part Number	Package	Quantity
GSDBAS16F	SOT-23	3000 PCS

Marking Information

Part Number	Package	Part Marking
GSDBAS16F	SOT- 23	5D

Maximum Ratings

(T_A=25°C Unless otherwise noted)

Symbol	Conditions	Value	Unit
V _{RRM}	Peak Repetitive Reverse Voltage	85	V
V _R	Reverse Voltage	75	V
I _F	Forward Current	215	mA
I _{FSM}	Peak Forward Surge Current, t = 1s t = 1μs	0.5 4	A
P _D	Total Power Dissipation(Note1)	350	mW
T _J	Junction Temperature	150	°C
T _{STG}	Storage Temperature Range	-55 to +150	°C

Electrical Characteristics

(T_A=25°C Unless otherwise noted)

Symbol	Conditions	Max	Unit
V _F	Forward Voltage (I _F =1.0mA)	715	mV
	(I _F =10mA)	855	
	(I _F =50mA)	1000	
	(I _F =150mA)	1250	
I _R	Reverse Current , V _R =25V	30	nA
	Reverse Current , V _R =75V	1	
	Reverse Current , (V _R =25V, T _J =150°C)	30	μA
	Reverse Current , (V _R =70V, T _J =150°C)	50	
C _d	Diode Capacitance (V _R =0V, f=1.0MHz),	2	pF
T _{rr}	Reverse Recovery Time I _F =10mA, V _R =6V , I _{rr} =1mA, R _L =100Ω	4	ns

Typical Characteristics

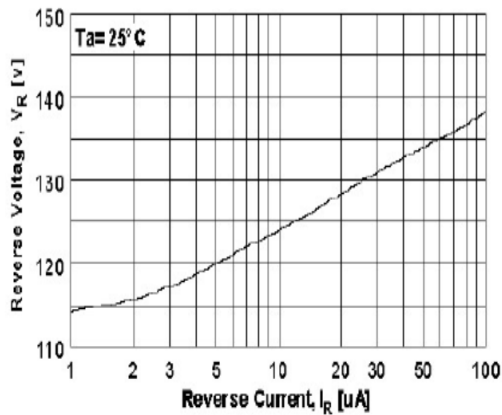


Figure 1. Reverse Voltage vs Reverse Current
BV - 1.0 to 100 uA

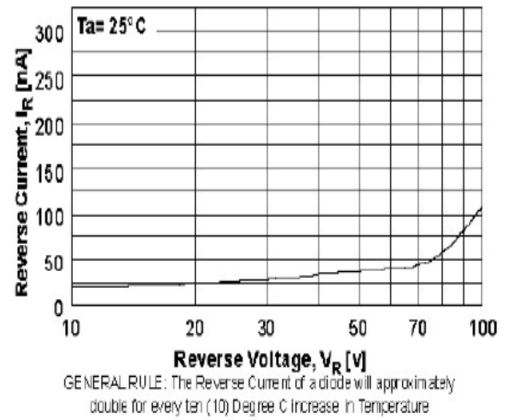


Figure 2. Reverse Current vs Reverse Voltage
IR - 10 to 100 V

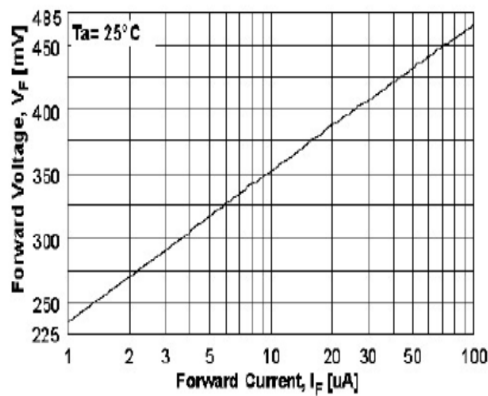


Figure 3. Forward Voltage vs Forward Current
VF - 1.0 to 100 uA

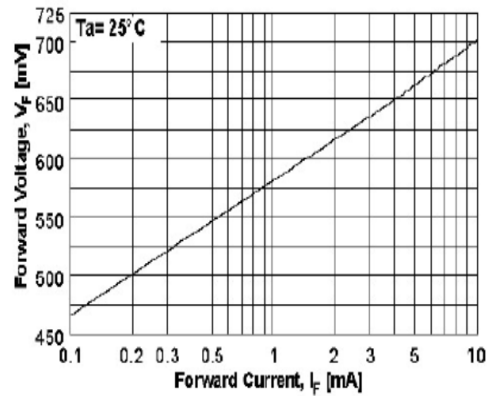


Figure 4. Forward Voltage vs Forward Current
VF - 0.1 to 10 mA

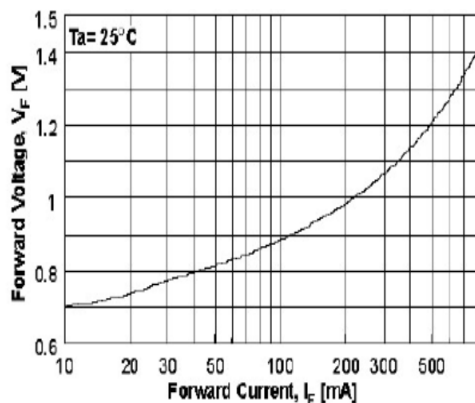


Figure 5. Forward Voltage vs Forward Current
VF - 10 - 800 mA

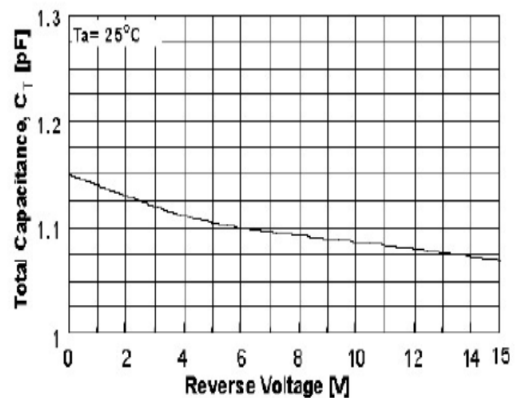
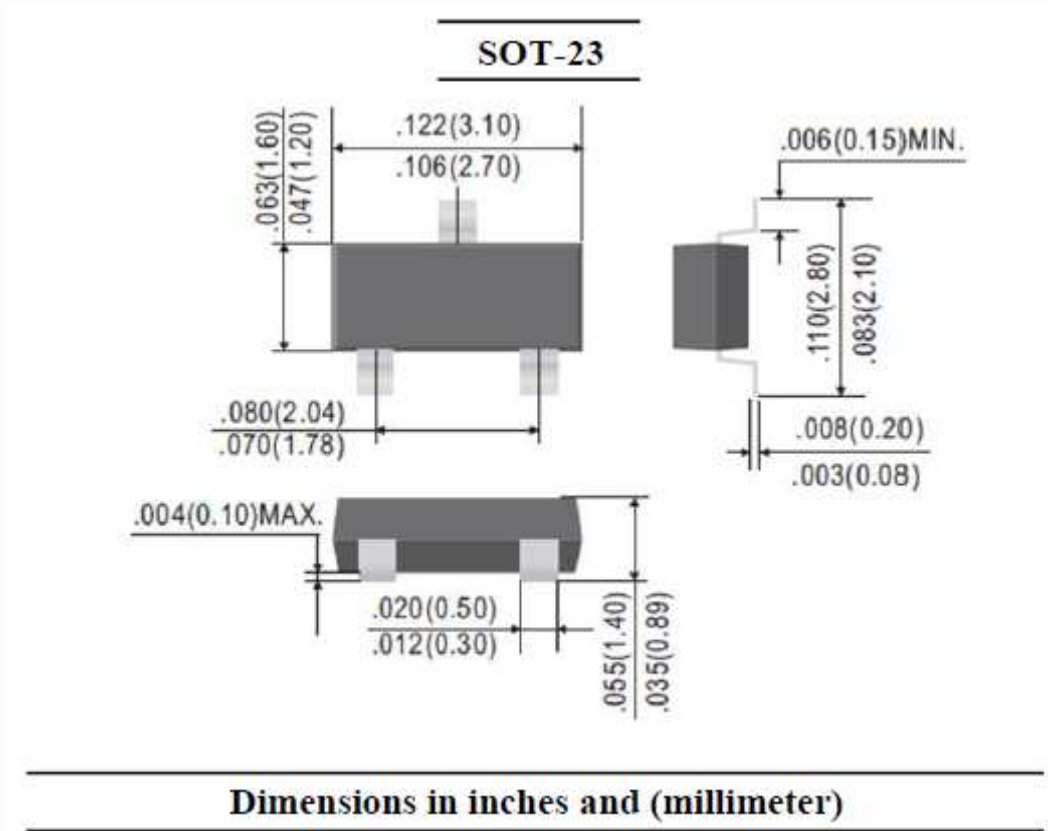


Figure 6. Total Capacitance





Package Dimension





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